
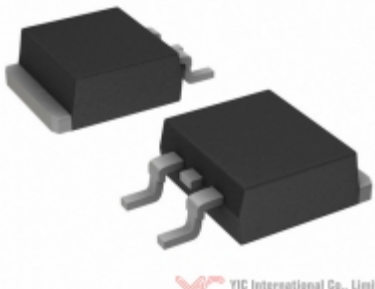






	<h2 style="color: red;">FQB55N10TM</h2> <p><b>Hersteller-Teilenummer:</b> <a href="#">FQB55N10TM</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Fairchild/ON Semiconductor</a></p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 100V 55A D2PAK</p> <p><b>Datenblätter:</b>  <a href="#">FQB55N10TM.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 42164 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">FQB55N10TM</a>
Hersteller	<a href="#">Fairchild/ON Semiconductor</a>
Beschreibung	MOSFET N-CH 100V 55A D2PAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	42164 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D <sup>2</sup> Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D <sup>2</sup> PAK (TO-263AB)
Verlustleistung (max)	3.75W (Ta), 155W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	55A (Tc)
Rds On (Max) @ Id, Vgs	26 mOhm @ 27.5A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	98nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	2730pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±25V
Verpackung	Tape & Reel (TR)

FQB55N10TM ist neu im Original, Suche FQB55N10TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB55N10TM Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB55N10TM: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <b>FQB55N10</b> FAIRCHI FQB55N10 FAIRCHI	 <b>FQB55N10TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 55A D2PAK	 <b>FQB55N06TM</b> Fairchild/ON Semiconductor MOSFET N-CH 60V 55A D2PAK	 <b>FQB52N25</b> FAIRCHILD FAIRCHILD TO-263
 <b>FQB5N15TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 150V 5.4A D2PAK	 <b>FQB5N15TM</b> Fairchild/ON Semiconductor MOSFET N-CH 150V 5.4A D2PAK	 <b>FQB55N06TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 55A D2PAK	 <b>FQB5N15</b> Fairchild/ON Semiconductor FQB5N15 FAIRCHILD

### heiße Teile

Mehr

FQB4N25TM	FQB4N20TM	FQB4N50TM	FQB4N50TM	FQB4N60C
FQB4N80TM	FQB4N80TM	FQB4N90TM	FQB4N90TM	FQB4P25TM
FQB4P25TM	FQB50N03	FQB50N06	FQB50N06C	FQB50N06L
FQB50N06LTM	FQB50N06LTM	FQB50N06M	FQB50N06TM	FQB50N06TM
FQB50N06TM-NL	FQB55N06TM	FQB55N06TM	FQB55N10	FQB55N10TM
FQB5N20L	FQB5N30TM	FQB5N30TM	FQB5N50C	FQB5N50CF
FQB5N50CTM	FQB5N50CTM	FQB5N60CTM	FQB5N60CTM	FQB5N90TM
FQB5N90TM	FQB5P10TM	FQB5P10TM	FQB630TM	FQB630TM
FQB65N06	FQB65N06TM	FQB65N06TM	FQB6N40C	FQB6N40CF
FQB6N40CTM	FQB6N40CTM	FQB6N50TM	FQB6N50TM	FQB6N60C

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